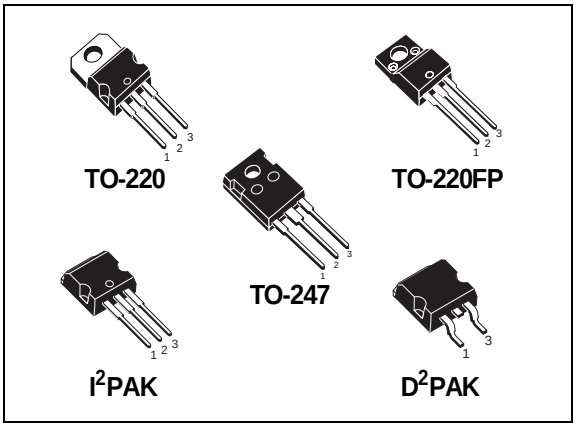
STP22NM60 - STF22NM60
STB22NM60 - STB22NM60-1 - STW22NM60

N-CHANNEL 600V - 0.19 Ω - 22A TO-220/FP/D²PAK/I²PAK/TO-247
MDmesh™Power MOSFET

ADVANCED DATA

TYPE	V_{DSS}	$R_{DS(on)}$	$R_{ds(on)}*Q_g$	I_D
STP22NM60	600 V	< 0.25 Ω	7.6 Ω*nC	22 A
STF22NM60	600 V	< 0.25 Ω	7.6 Ω*nC	22 A
STB22NM60	600 V	< 0.25 Ω	7.6 Ω*nC	22 A
STB22NM60-1	600 V	< 0.25 Ω	7.6 Ω*nC	22 A
STW22NM60	600 V	< 0.25 Ω	7.6 Ω*nC	22 A

- TYPICAL $R_{DS}(on)$ = 0.19Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE



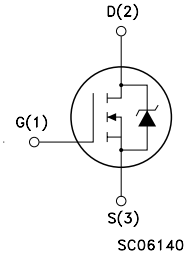
DESCRIPTION

This improved version of MDmesh™ which is based on Multiple Drain process represents the new benchmark in high voltage MOSFETs. The resulting product exhibits even lower on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall performances that are significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP22NM60	P22NM60	TO-220	TUBE
STF22NM60	F22NM60	TO-220FP	TUBE
STB22NM60	B22NM60T4	D²PAK	TAPE & REEL
STB22NM60-1	B22NM60-1	I²PAK	TUBE
STW22NM60	W22NM60	TO-247	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit
		STP22NM60 STB22NM60/1	STF22NM60	STW22NM60	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600			V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	600			V
V_{GS}	Gate- source Voltage	±30			V
I_D	Drain Current (continuous) at T_C = 25°C	22	22 (*)	22	A
I_D	Drain Current (continuous) at T_C = 100°C	12.6	12.6 (*)	12.6	A
I_{DM} (•)	Drain Current (pulsed)	80	80(*)	80	A
P_{TOT}	Total Dissipation at T_C = 25°C	192	45	210	W
	Derating Factor	1.2	0.36	1.2	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	15			V/ns
V_{ISO}	Insulation Winthstand Voltage (DC)	--	2500	--	V
T_{stg}	Storage Temperature	–65 to 150			°C
T_j	Max. Operating Junction Temperature	150			°C

(•) Pulse width limited by safe operating area; (*)Limited only by maximum temperature allowed

(1) I_{SD} ≤22A, di/dt ≤400A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX.}$

THERMAL DATA

			TO-220/D²PAK/I²PAK/TO-247	TO-220FP	
Rthj-case	Thermal Resistance Junction-case	Max	0.65	2.8	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	11	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	650	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	600			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30 V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 11 A		0.19	0.25	Ω

ELECTRICAL CHARACTERISTICS (CONTINUE)

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 11$ A		TBD		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V$, f = 1 MHz, $V_{GS} = 0$		1590 803 52		pF pF pF
$C_{oss\ eq.}$ (2)	Equivalent Output Capacitance	$V_{GS} = 0V$, $V_{DS} = 0V$ to 400V		130		pF
R_g	Gate Input Resistance	f=1 MHz Gate DC Bias=0 Test Signal Level=20mV Open Drain		1.6		Ω

(1) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.

(*) $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 200$ V, $I_D = 11$ A $R_G = 4.7\Omega$ $V_{GS} = 10$ V (see test circuit, Figure 3)		25 20		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400$ V, $I_D = 22$ A, $V_{GS} = 10$ V		40 11 25	71	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 480$ V, $I_D = 22$ A, $R_G = 4.7\Omega$, $V_{GS} = 10$ V (see test circuit, Figure 5)		13		ns
t_f	Fall Time			15		ns
t_c	Cross-over Time			26		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				20	A
I_{SDM} (2)	Source-drain Current (pulsed)				80	A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 22$ A, $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 22$ A, di/dt = 100 A/µs, $V_{DD} = 100$ V, $T_j = 25°C$ (see test circuit, Figure 5)		416 5.6 27		ns µC A
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 22$ A, di/dt = 100 A/µs, $V_{DD} = 100$ V, $T_j = 150°C$ (see test circuit, Figure 5)		544 7.3 28		ns µC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

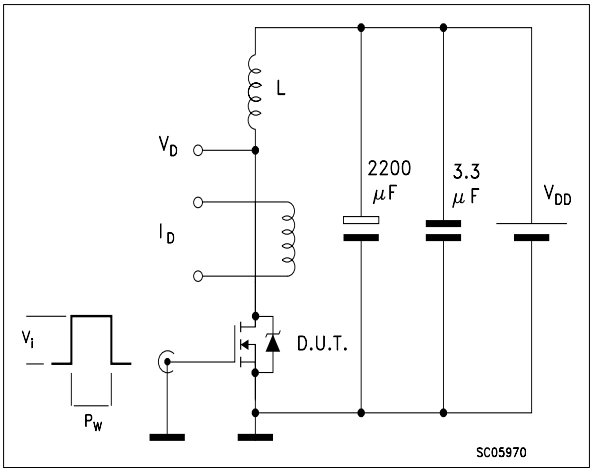


Fig. 2: Unclamped Inductive Waveform

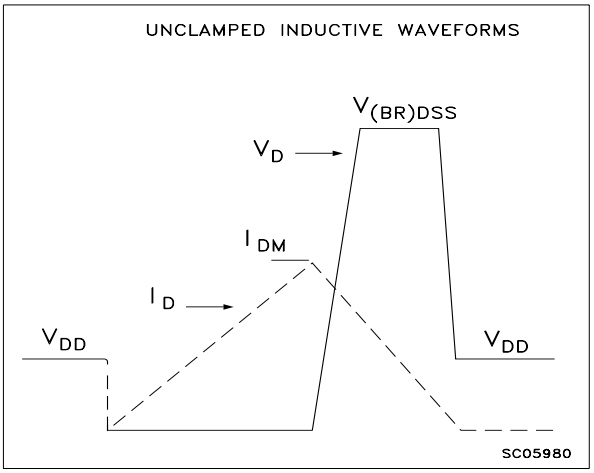


Fig. 3: Switching Times Test Circuit For Resistive Load

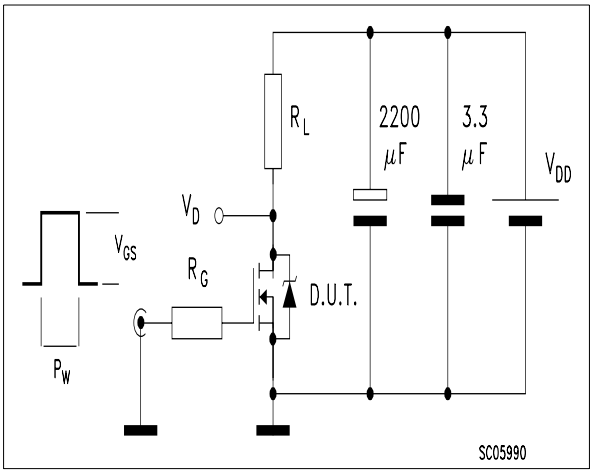


Fig. 4: Gate Charge test Circuit

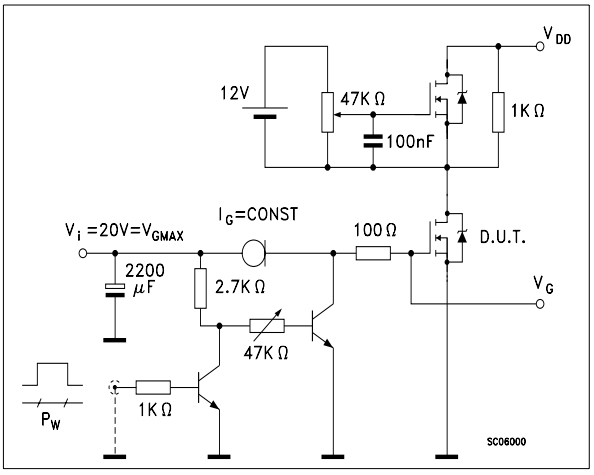
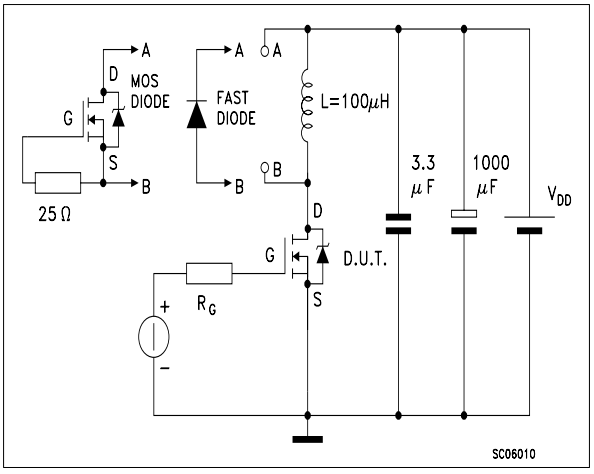
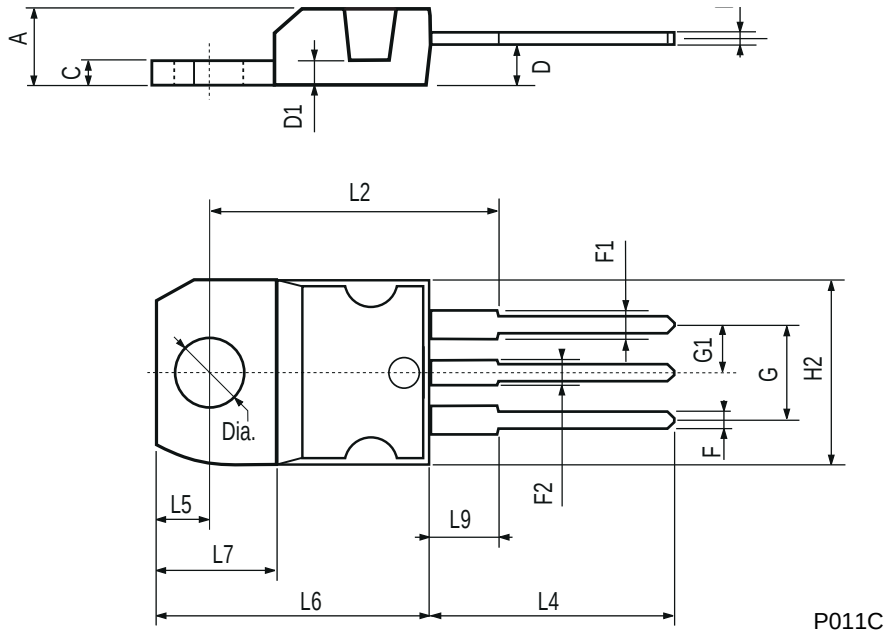


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



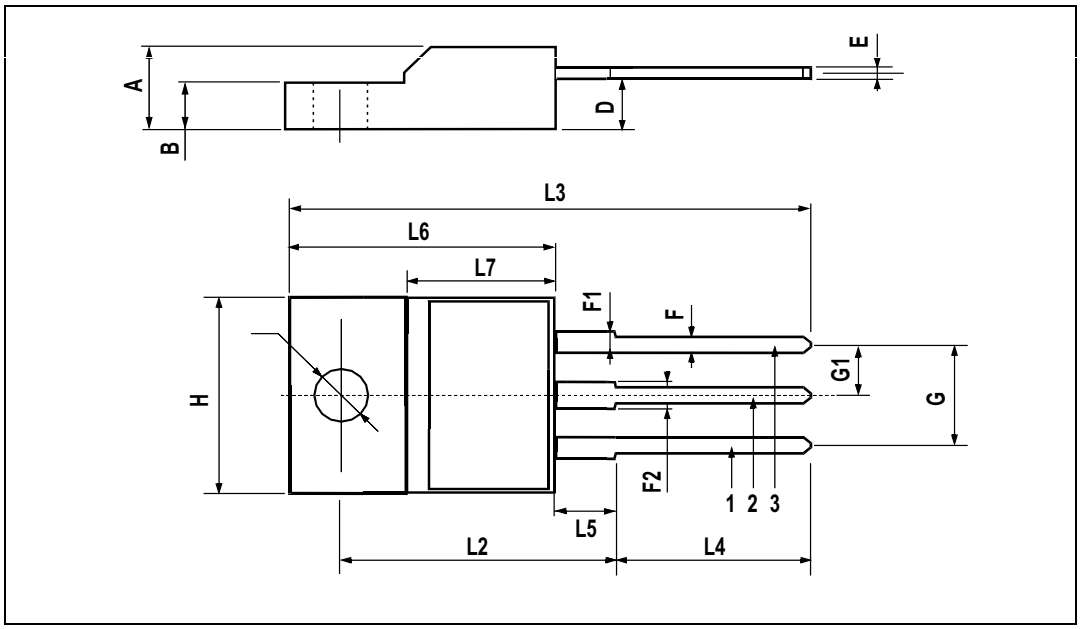
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



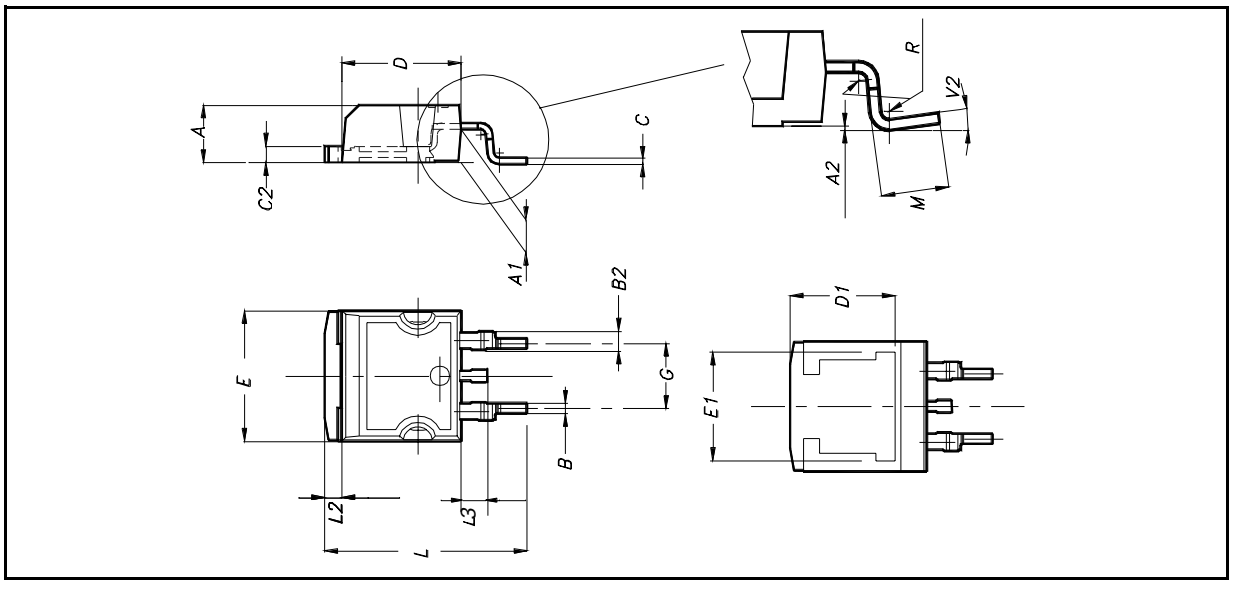
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



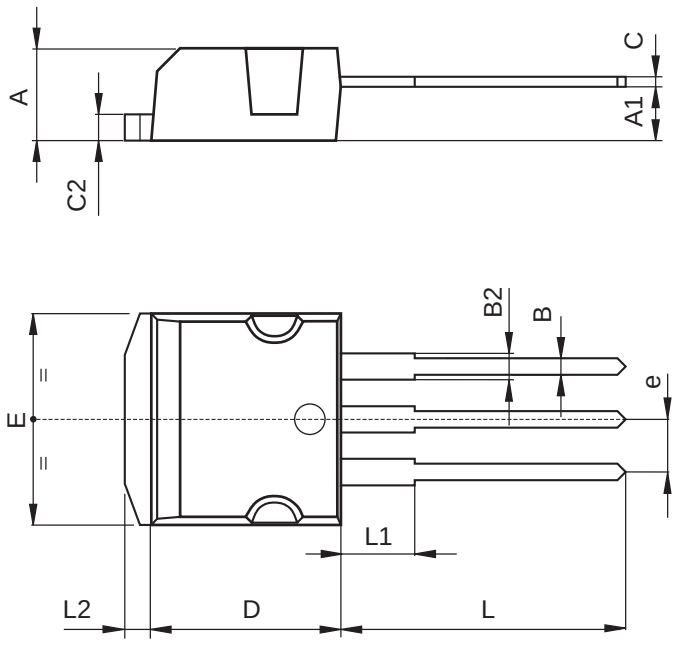
D^2PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		8º			



TO-262 (I^2PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055



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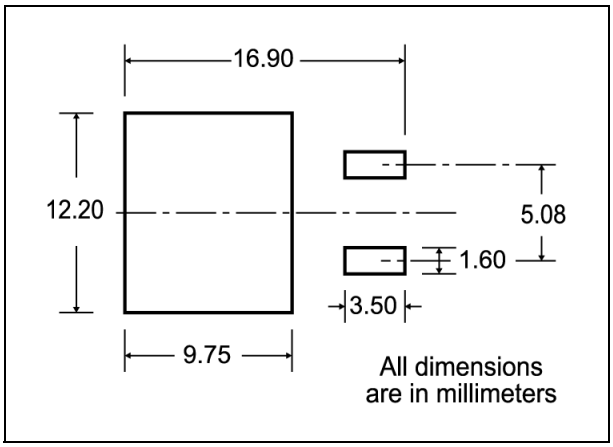
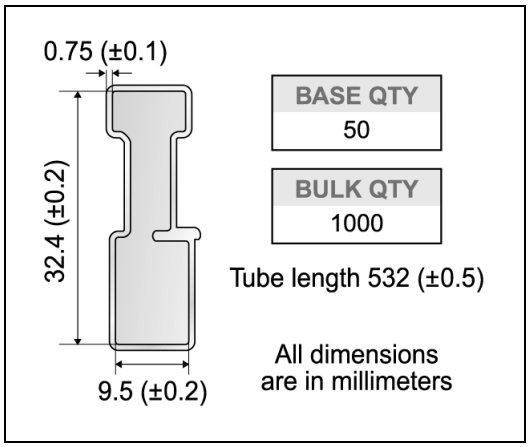
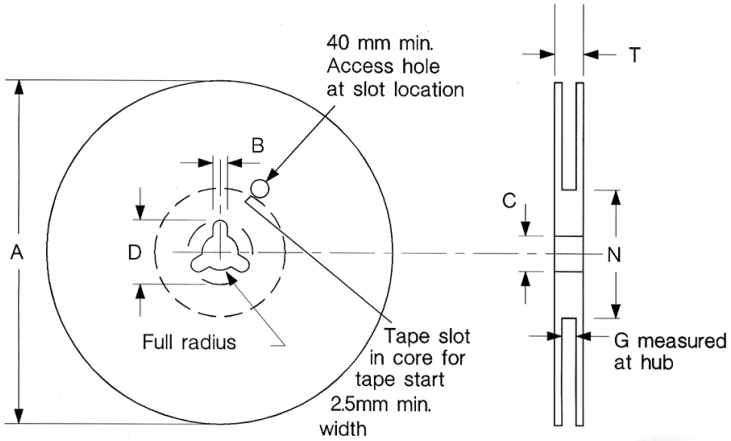
D^2PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



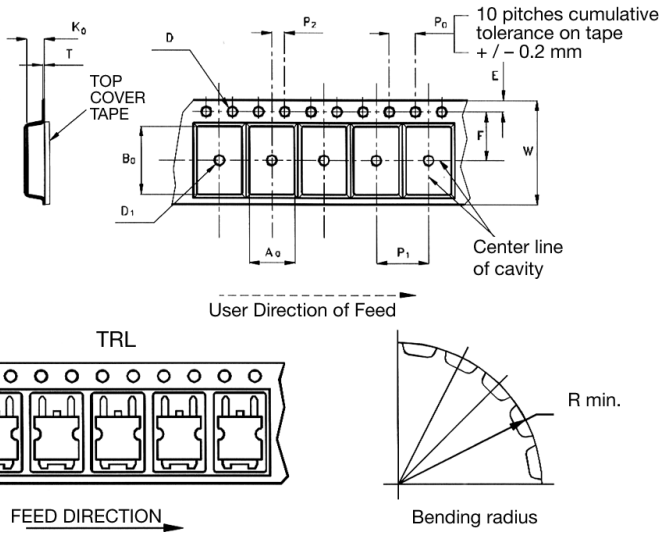
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

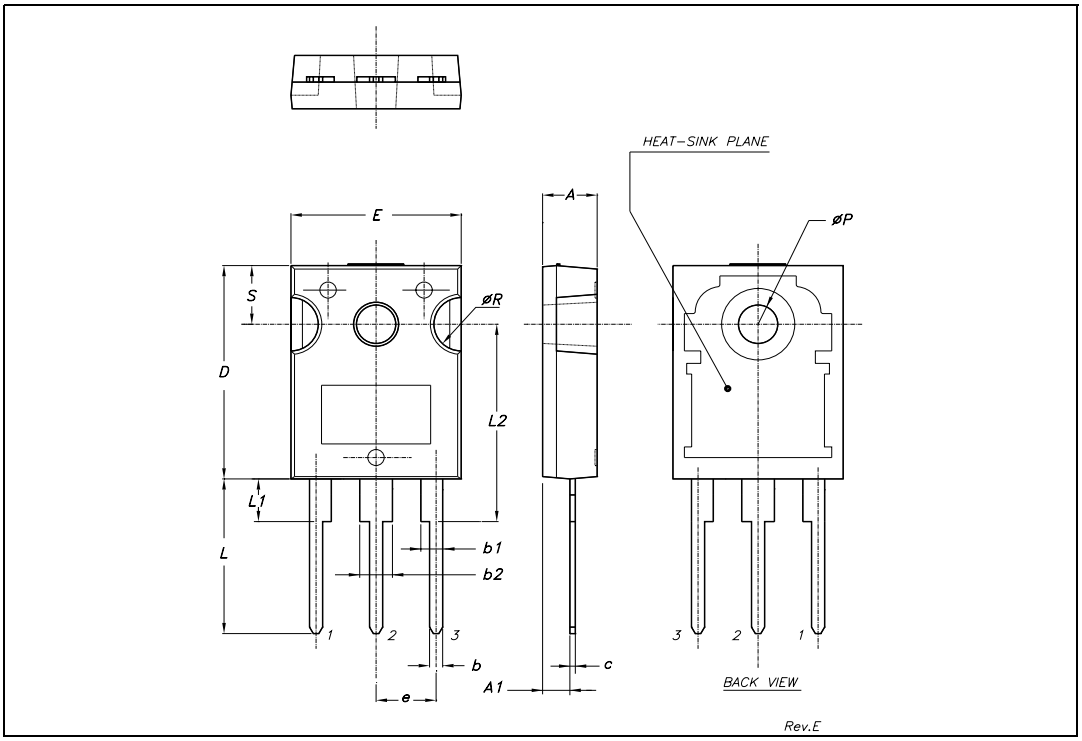
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



* on sales type

TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



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